



# JMP(C.F.H.I.K)8N60B

## Description

### JMP N-channel MOSFET

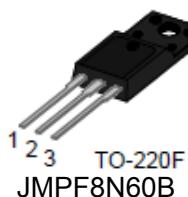
#### Features

- 600V,8A
- $R_{DS(ON)} = 1.05\Omega$  (Typ.) @  $V_{GS} = 10V$ ,  $I_D = 4A$
- Fast Switching
- Improved dv/dt Capability
- 100% Avalanche Tested

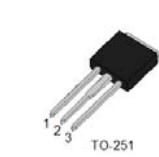
#### Application

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply(UPS)
- Power Factor Correction (PFC)

#### Package



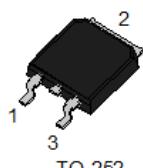
JMPF8N60B



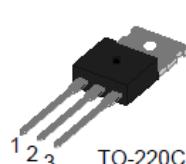
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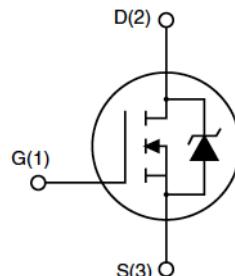
JMPI8N60B



JMPK8N60B



JMPC8N60B



## Absolute Maximum Ratings ( $T_c=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max.		Units
		TO-251/TO-252/ TO-251-4R/TO-220C	TO-220F	
$V_{DSS}$	Drain-Source Voltage	600		V
$V_{GSS}$	Gate-Source Voltage	$\pm 30$		V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	8	A
		$T_c = 100^\circ C$	5	A
$I_{DM}$	Pulsed Drain Current <sup>note1</sup>	32		A
$E_{AS}$	Single Pulsed Avalanche Energy <sup>note2</sup>	198		mJ
$I_{AR}$	Avalanche Current	4.5		A
$E_{AR}$	Repetitive Avalanche Energy	40		mJ
$P_D$	Power Dissipation	$T_c = 25^\circ C$	97	W
$R_{eJC}$	Thermal Resistance, Junction to Case	1.29	1.98	$^\circ C/W$
$R_{eJA}$	Thermal Resistance, Junction to Ambient	60	62.5	$^\circ C/W$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150		$^\circ C$



# JMP(C.F.H.I.K)8N60B

## Electrical Characteristics ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu\text{A}$	600	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	-	-	1	$\mu\text{A}$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 30V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D=250\mu\text{A}$	2.0	-	4.0	V
$R_{DS(\text{on})}$	Static Drain-Source on-Resistance note3	$V_{GS} = 10V, I_D = 4A$	-	1.05	1.3	$\Omega$
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0\text{MHz}$	-	891	-	pF
$C_{oss}$	Output Capacitance		-	110	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	14	-	pF
$Q_g$	Total Gate Charge	$V_{DD} = 480V, I_D = 8A, V_{GS} = 10V$	-	22	-	nC
$Q_{gs}$	Gate-Source Charge		-	4.3	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	13	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 300V, I_D = 8A, R_G = 25\Omega$	-	15	-	ns
$t_r$	Turn-on Rise Time		-	18	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	80	-	ns
$t_f$	Turn-off Fall Time		-	35	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_s$	Maximum Continuous Drain to Source Diode Forward Current	-	-	8	A	
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	-	32	A	
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_{SD} = 8A$	-	-	1.4	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0V, I_s = 8A, di/dt = 100A/\mu\text{s}$	-	310	-	ns
$Q_{rr}$	Reverse Recovery Charge		-	4.1	-	$\mu\text{C}$

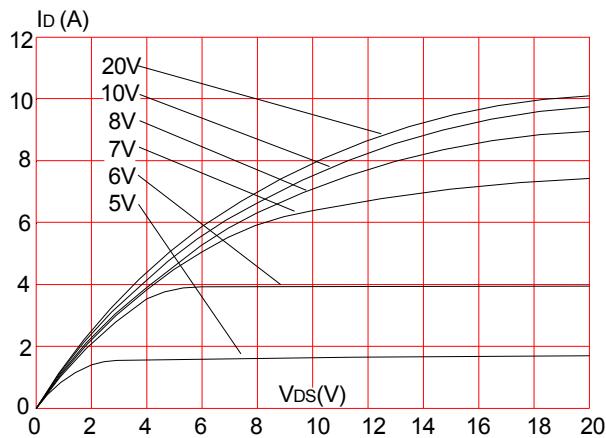
Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2.  $I_{AS} = 4.5A, V_{DD} = 50V, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$

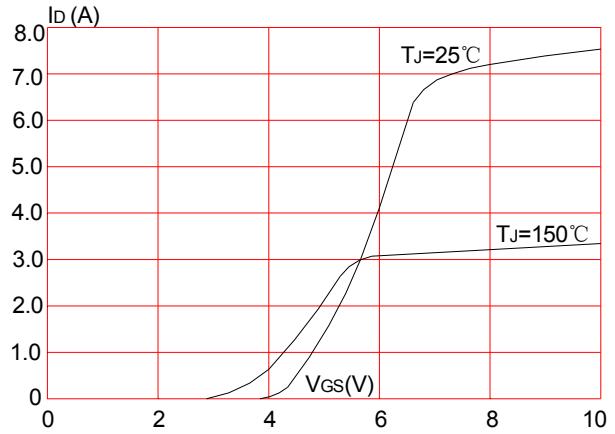
3. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 1\%$

## Typical Performance Characteristics

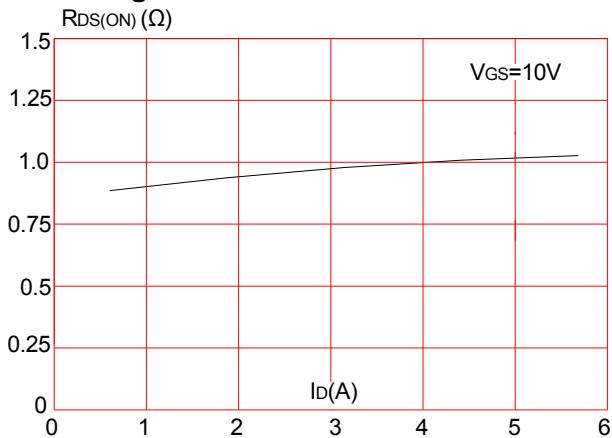
**Figure1:** Output Characteristics



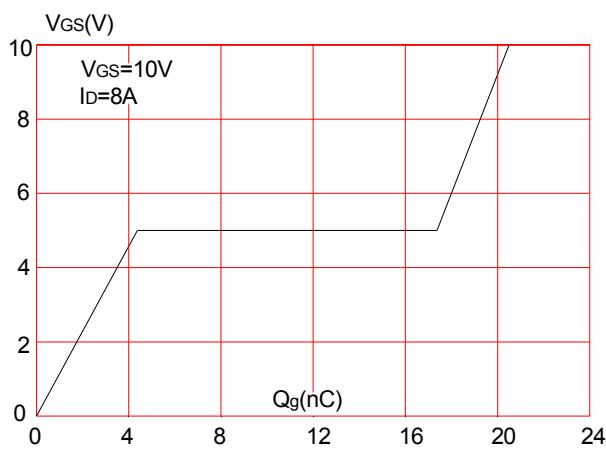
**Figure 2:** Typical Transfer Characteristics



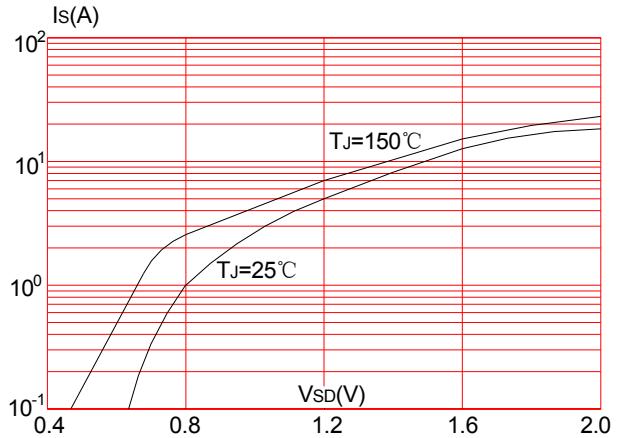
**Figure 3:** On-resistance vs. Drain Current



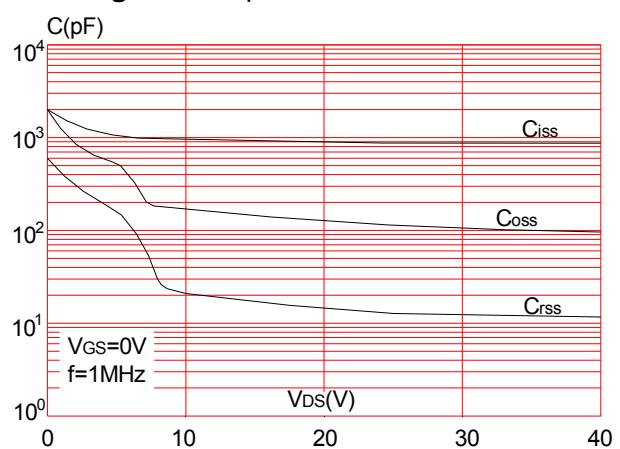
**Figure 5:** Gate Charge Characteristics



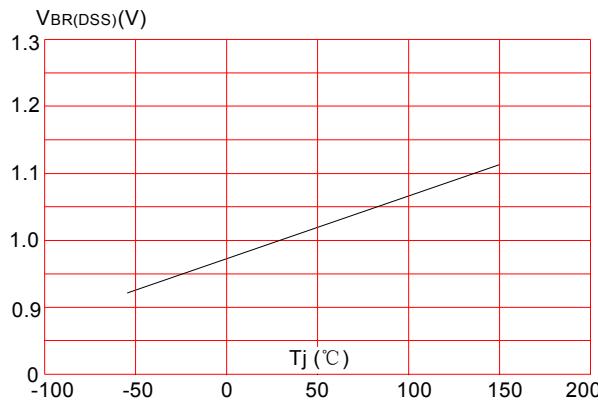
**Figure 4:** Body Diode Characteristics



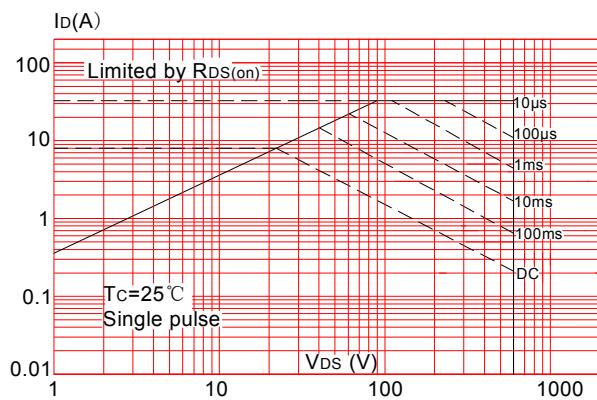
**Figure 6:** Capacitance Characteristics



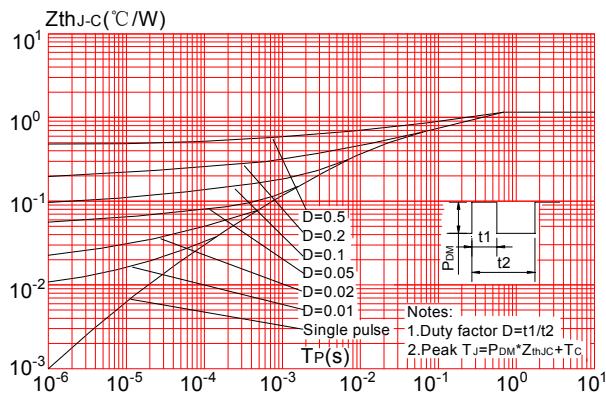
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



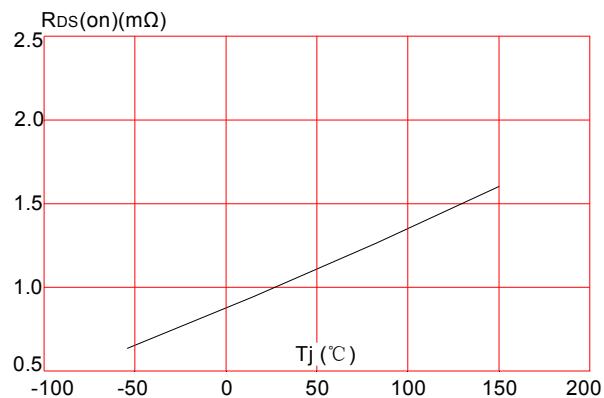
**Figure 9:** Maximum Safe Operating Area



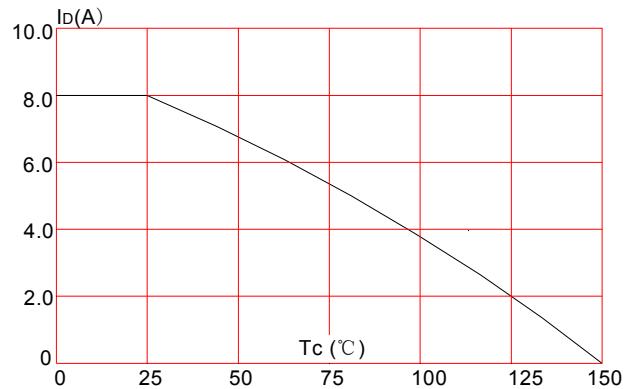
**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-251, TO-252, TO-220C, TO-251-4R)



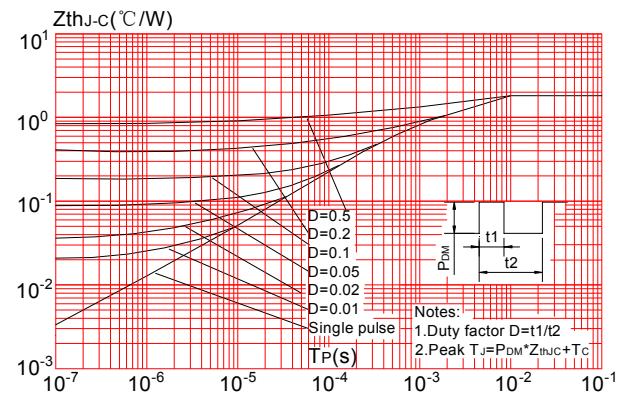
**Figure 8:** Normalized on Resistance vs. Junction Temperature



**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature



**Figure.12:** Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-220F)



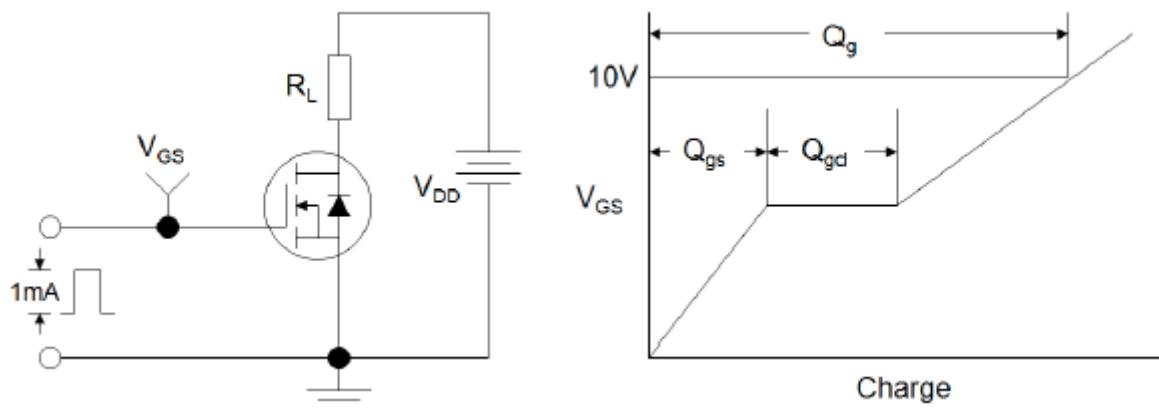


Figure1:Gate Charge Test Circuit & Waveform

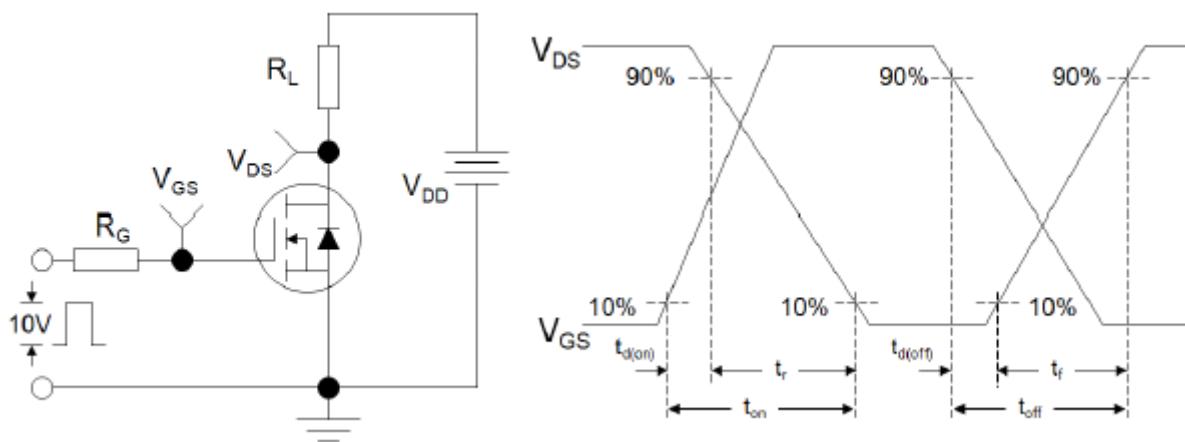


Figure 2: Resistive Switching Test Circuit & Waveforms

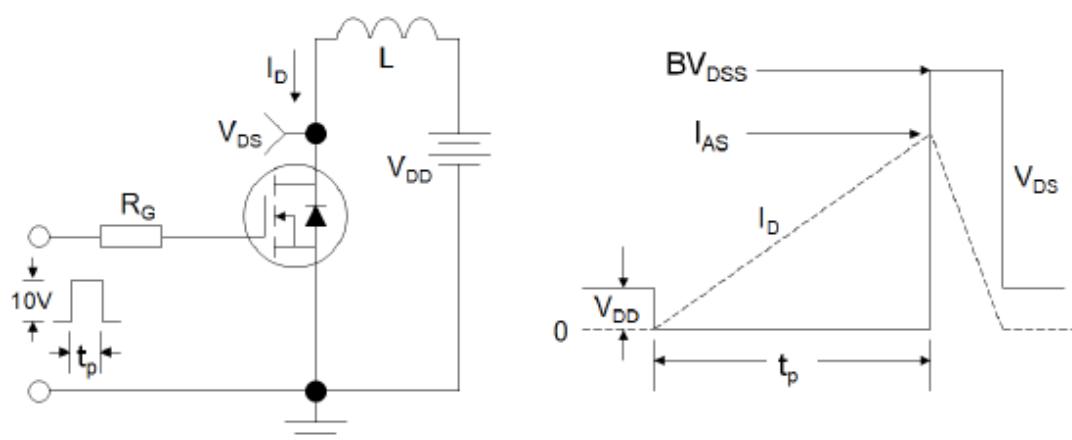
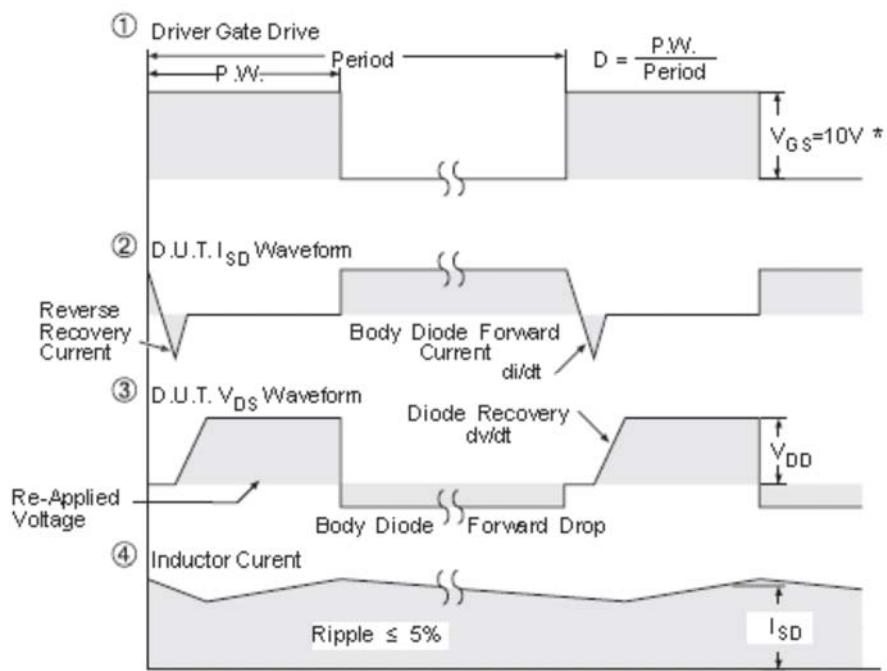
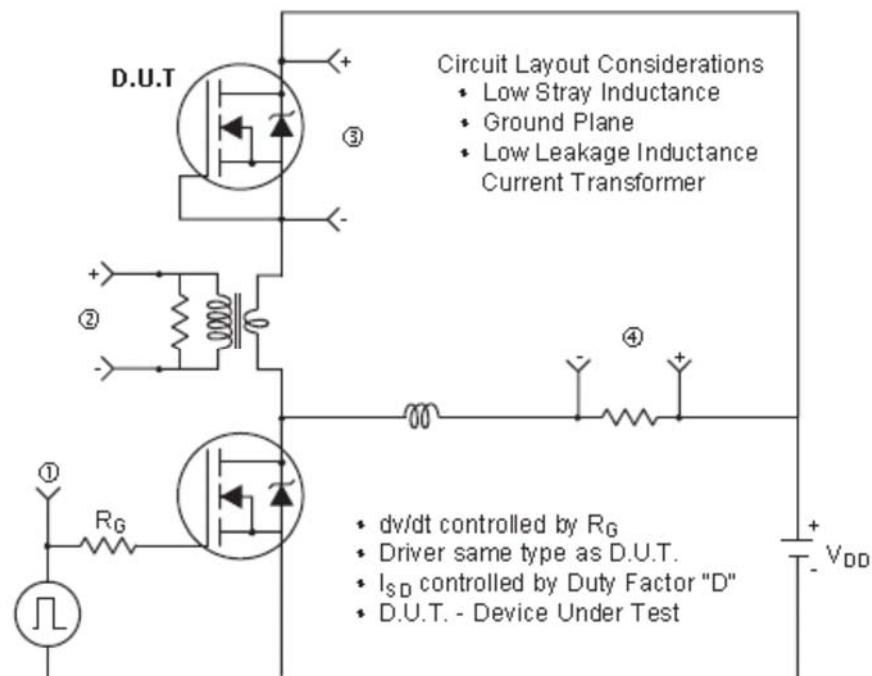


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

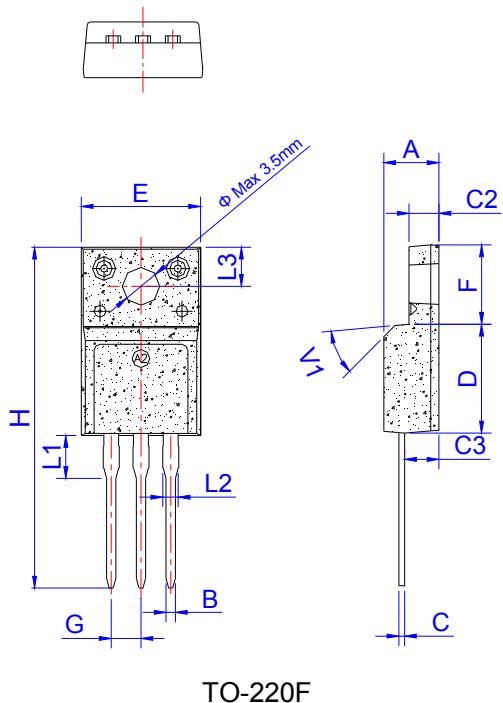


\*  $V_{GS} = 5V$  for Logic Level Devices

Figure 4:Peak Diode Recovery dv/dt Test Circuit & Waveforms (For N-channel)



## Package Mechanical Data



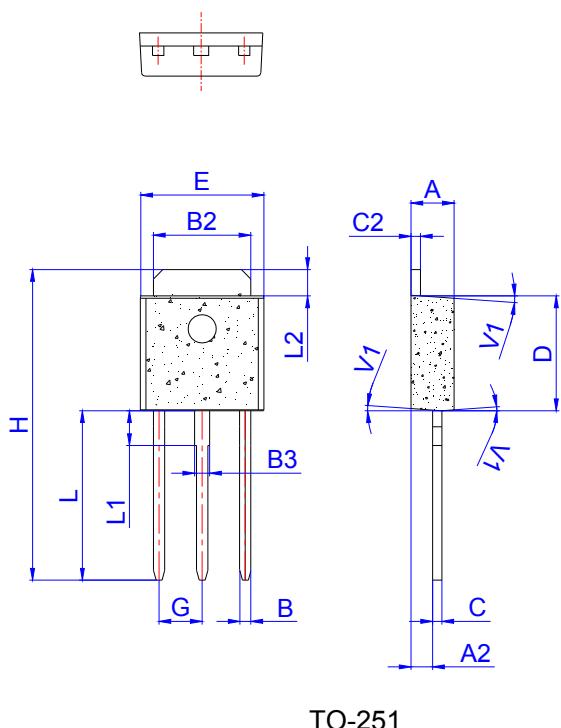
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

## Package Information -TO-220F

OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TUBE	50	1,000	8,000



## Package Mechanical Data



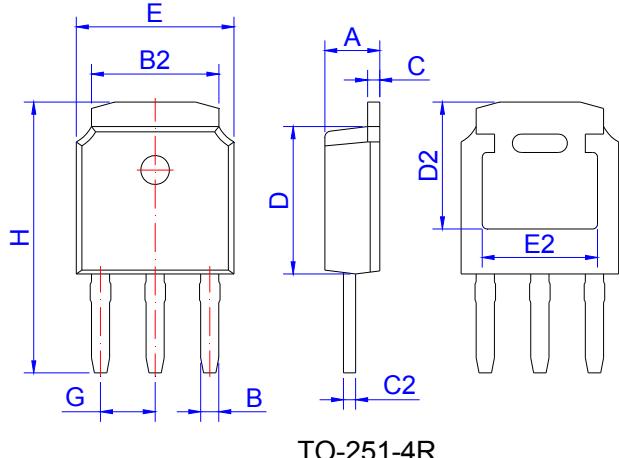
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.90		1.20	0.035		0.047
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
B3	0.76		0.85	0.030		0.033
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G		2.30			0.091	
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		1.90	0.071		0.075
L2	1.37		1.50	0.054		0.059
V1		4°			4°	

## Package Information -TO-251

OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TUBE	80	4,000	32,000



## Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10	2.30	2.50	0.083	0.091	0.098
B	0.66	0.76	0.86	0.026	0.030	0.034
B2	5.15	5.33	5.48	0.203	0.210	0.216
C	0.44	0.51	0.58	0.017	0.020	0.023
C2	0.44	0.51	0.58	0.017	0.020	0.023
D	5.90	6.10	6.30	0.232	0.240	0.248
D2	5.30 REF			0.209 REF		
E	6.40	6.60	6.80	0.252	0.260	0.268
E2	4.83 REF			0.190 REF		
G	2.19	2.29	2.39	0.086	0.090	0.094
H	10.60	11.20	11.80	0.417	0.441	0.465

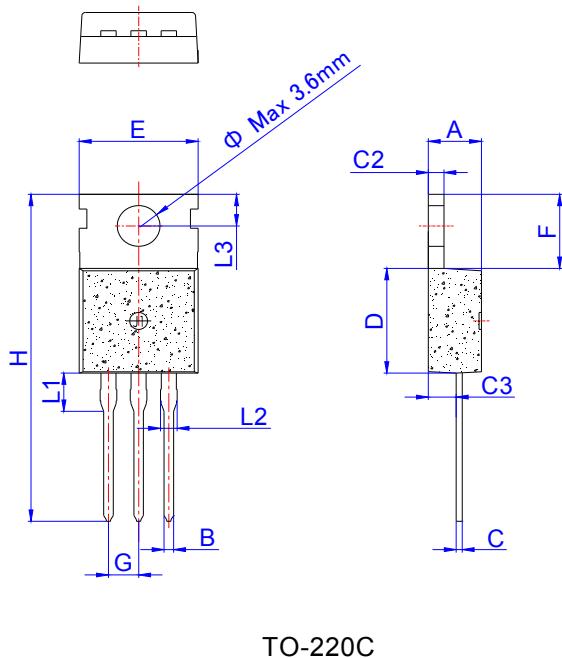
## Package Information -TO-251-4R

OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TUBE	80	4,000	32,000





## Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		1.181
B	0.70		0.90	0.027		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.086		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	11.0		11.7
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	

## Package Information -TO-220C

OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TUBE	50	1,000	8,000

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